

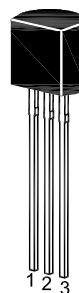
# ST 2SC2901

## NPN Silicon Epitaxial Planar Transistor

for general purpose amplifier and high speed switching applications.

The transistor is subdivided into two groups L and K, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

| Parameter                            | Symbol    | Value         | Unit             |
|--------------------------------------|-----------|---------------|------------------|
| Collector Base Voltage               | $V_{CBO}$ | 40            | V                |
| Collector Emitter Voltage            | $V_{CES}$ | 40            | V                |
| Collector Emitter Voltage            | $V_{CEO}$ | 15            | V                |
| Emitter Base Voltage                 | $V_{EBO}$ | 5             | V                |
| Collector Current                    | $I_C$     | 200           | mA               |
| Collector Current (10 $\mu$ s pulse) | $I_{CP}$  | 500           | mA               |
| Power Dissipation                    | $P_{tot}$ | 600           | mW               |
| Junction Temperature                 | $T_j$     | 150           | $^\circ\text{C}$ |
| Storage Temperature Range            | $T_{stg}$ | - 55 to + 150 | $^\circ\text{C}$ |

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter   | Symbol                    | Min.     | Typ. | Max. | Unit          |   |
|---|---------------------------|----------|------|------|---------------|---|
| DC Current Gain<br>at $V_{CE} = 1\text{ V}$ , $I_C = 10\text{ mA}$  | Current Gain Group L<br>K | $h_{FE}$ | 40   | -    | 120           | - |
|   |                           | $h_{FE}$ | 100  | -    | 200           | - |
| Collector Base Cutoff Current<br>at $V_{CB} = 20\text{ V}$  | $I_{CBO}$                 | -        | -    | 0.1  | $\mu\text{A}$ |   |
| Emitter Base Cutoff Current<br>at $V_{EB} = 3\text{ V}$   | $I_{EBO}$                 | -        | -    | 0.1  | $\mu\text{A}$ |   |
| Collector Emitter Saturation Voltage<br>at $I_C = 10\text{ mA}$ , $I_B = 1\text{ mA}$                                 | $V_{CE(sat)}$             | -        | 0.15 | 0.25 | V             |   |
| Base Emitter Saturation Voltage<br>at $I_C = 10\text{ mA}$ , $I_B = 1\text{ mA}$                                      | $V_{BE(sat)}$             | -        | 0.8  | 0.85 | V             |   |
| Turn-on Time<br>at $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = 3\text{ mA}$ , $-V_{BE} = 1.5\text{ V}$   | $t_{on}$                  | -        | 8    | 12   | ns            |   |
| Storage Time<br>at $I_C = 10\text{ mA}$ , $I_{B1} = -I_{B2} = 10\text{ mA}$   | $t_{stg}$                 | -        | 6    | 13   | ns            |   |
| Turn-off Time<br>at $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = 3\text{ mA}$ , $-I_{B2} = 1.5\text{ mA}$ | $t_{off}$                 | -        | 12   | 18   | ns            |   |
| Gain Bandwidth Product<br>at $V_{CE} = 10\text{ V}$ , $-I_E = 10\text{ mA}$ , $f = 100\text{ MHz}$                    | $f_T$                     | 500      | 750  | -    | MHz           |   |
| Output Capacitance<br>at $V_{CB} = 5\text{ V}$ , $f = 1\text{ MHz}$   | $C_{ob}$                  | -        | 1.8  | 4    | pF            |   |

